

PRODUCT/PROCESS CHANGE NOTIFICATION

PCN MPA-PMT/06/1871 Notification Date 07/14/2006

New Subcontractor location (GEM) for Low Voltage DPAK Power Mosfets PMT - POWER MOSFET PMT - POWER MOSFET

Table 1. Change Identification

| Product Identification (Product Family/Commercial Product) | see attached list |
|--|--|
| Type of change | Package assembly location change |
| Reason for change | Capacity Extension |
| Description of the change | Power Mosfet Division has decided to set up a new Subcontractor (GEM). Devices in DPAK, assembled in ST House plant, will be manufactured also in Subcontractor GEM. |
| Product Line(s) and/or Part Number(s) | See attached |
| Description of the Qualification Plan | See attached |
| Change Product Identification | See "GL" on trace code, "G" is China, "L" is GEM |
| Manufacturing Location(s) | |

Table 2. Change Implementation Schedule

| Forecasted implementation date for change | 25-Sep-2006 |
|--|-------------|
| Forecasted availability date of samples for customer | 26-Jun-2006 |
| Forecasted date for STMicroelectronics change Qualification Plan results availability | 26-Jun-2006 |
| Estimated date of changed product first shipment | 26-Jun-2006 |

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Table 3. Change Responsibility

| | Name | Signature | Date |
|----------------------------|------------------|-----------|------------|
| Division Product Manager | lan Wilson | | Jul.11 ,06 |
| Division Q.A. Manager | Giuseppe Falcone | | Jul.11 ,06 |
| Division Marketing Manager | Maurizio Giudice | | Jul.11 ,06 |

| Table | 4 I | iet | Ωf | Atta | chn | nante |
|-------|------------|-----|----|------|-----|-------|
| | | | | | | |

| Customer Part numbers list | |
|----------------------------|--|
| Qualification Plan results | |

| Customer Acknowledgement of Receipt | PCN MPA-PMT/06/1871 |
|--|---|
| Please sign and return to STMicroelectronics | Sales Office Notification Date 07/14/2006 |
| □ Qualification Plan Denied | Name: |
| □ Qualification Plan Approved | Title: |
| | Company: |
| □ Change Denied | Date: |
| □ Change Approved | Signature: |
| Remark | |
| | |
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RELIABILITY EVALUATION ON DPAK ASSEMBLED IN GEM



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Introduction

This report aims at the internal qualification of the package DPAK assembled in sub-contractor GEM

The Qualification Reliability test trials have been performed in ST Catania Site.

The evaluation results meet ST products qualification targets, therefore the DPAK is qualified in GEM.

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Test Vehicles:

| Product Lines | Main Sales Types |
|---------------|------------------|
| 432C | STD55NH2LLT4 |
| E33N | STD17NF03LT4 |
| 3L2B | STD38NH02LT4 |



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Failure Criteria:

A failed component is a device which becomes inoperative during the test or it fails on meeting the end limits foreseen in the device specification, for one or more than the parameters here below reported

| Parameter Power MOSFET |
|------------------------|
|------------------------|

Drain Leakage Current (Idss)
Gate Leakage Current (Igss)
Threshold Voltage (Vgs(th)
Forward On Voltage (Vsd)
Drain Source On Voltage (Vds(on))
Drain Source Breakdown Voltage (Bvdss)



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Reliability Evaluation Plan and results

D.U.T.: STD55NH2LLT4 LINE: 432C PACKAGE: DPAK

| Test | Conditions | S.S. | Requirement | Results |
|--|---|----------------|--|---|
| PRECONDITIONING OF SMD DEVICES Before TC/THB/ENV. SEQ. | DRYNG 1H @ 125°C STORE 168H @ TA=85°C RH=85% Reflow @ 260°C 3 times | 204 x 1 Lot | Parameter deviation within spec. limits at end of preconditioning. | No parameter deviation out of spec. limits at end of preconditioning. |
| H.T.S. | TA=175℃ | 77 x 1 Lot | Parameter deviation within spec. limits at 1000 hours. | No parameter deviation out of spec. limits at 1000 hours. |
| T.H.B. | D.U.T. SMD PRECONDITIONED TA=85℃ - RH=85% Vbias= 20V | 77 x 1 Lot | Parameter deviation within spec. limits at 1000 hours. | No parameter deviation out of spec. limits at 1000 hours. |
| H.T.R.B. | T.A.=175℃ Vdd=20V | 77 x 1 Lot | Parameter deviation within spec. limits at 1000 hours. | No parameter deviation out of spec. limits at 1000 hours. |
| H.T.F.B. | TA=150℃ Vgss=16V | 77 x 1 Lot | Parameter deviation within spec. limits at 1000 hours. | No parameter deviation out of spec. limits at 1000 hours. |
| PRESSURE POT | TA=121℃ - PA=2Atm | 77 x 1 Lot | Parameter deviation within spec. limits at 96 hours. | No parameter deviation out of spec. limits at 96 hours. |
| THERMAL CYCLES AIR TO AIR | D.U.T. SMD PRECONDITIONED TA=-65℃ TO 150℃ 1 HOUR / CYCLE | 77 x 1 Lot | Parameter deviation within spec. limits at 500 cycles. | No parameter deviation out of spec. limits at 500 cy |
| THERMAL FATIGUE | ΔTC=105℃ - Pd=2W | 77 x 1 Lot | Parameter deviation within spec. limits at 10k cycles. | No parameter deviation out of spec. limits at 10Kcy. |
| ENVIRONMENTAL SEQUENCE | D.U.T. SMD PRECONDITIONED 100 THERMAL CYCLES + 96H PP | 50 x 1 Lot | Parameter deviation within spec. limits at end of test. | No parameter deviation out of spec. limits at end of test. |

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Reliability Evaluation Plan and results

D.U.T.: STD17NF03LT4 LINE: E33N PACKAGE: DPAK

| Test | Conditions | S.S. | Requirement | Results |
|--|---|----------------|--|---|
| PRECONDITIONING OF SMD DEVICES Before TC/THB/ENV. SEQ. | DRYNG 1H @ 125°C STORE 168H @ TA=85°C RH=85% Reflow @ 260°C 3 times | 204 x 1 Lot | Parameter deviation within spec. limits at end of preconditioning. | No parameter deviation out of spec. limits at end of preconditioning. |
| H.T.S. | TA=175℃ | 77 x 1 Lot | Parameter deviation within spec. limits at 1000 hours. | No parameter deviation out of spec. limits at 1000 hours. |
| T.H.B. | D.U.T. SMD PRECONDITIONED TA=85℃ - RH=85% Vbias= 24V | 77 x 1 Lot | Parameter deviation within spec. limits at 1000 hours. | No parameter deviation out of spec. limits at 1000 hours. |
| H.T.R.B. | T.A.=175℃ Vdd=24V | 77 x 1 Lot | | No parameter deviation out of spec. limits at 1000 hours. |
| H.T.F.B. | TA=150℃ Vgss=16V | 77 x 1 Lot | | No parameter deviation out of spec. limits at 1000 hours. |
| PRESSURE POT | TA=121℃ - PA=2Atm | 77 x 1 Lot | Parameter deviation within spec. limits at 96 hours. | No parameter deviation out of spec. limits at 96 hours. |
| THERMAL CYCLES AIR TO AIR | D.U.T. SMD PRECONDITIONED TA=-65℃ TO 150℃ 1 HOUR / CYCLE | 77 x 1 Lot | | No parameter deviation out of spec. limits at 500 cy |
| THERMAL FATIGUE | ΔTC=105℃ - Pd=2W | 77 x 1 Lot | Parameter deviation within spec. limits at 10k cycles. | No parameter deviation out of spec. limits at 10Kcy. |
| ENVIRONMENTAL SEQUENCE | D.U.T. SMD PRECONDITIONED 100 THERMAL CYCLES + 96H PP | 50 x 1 Lot | Parameter deviation within spec. limits at end of test. | No parameter deviation out of spec. limits at end of test. |

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Reliability Evaluation Plan and results

D.U.T.: STD38NH02LT4 LINE: 3L2B PACKAGE: DPAK

| Test | Conditions | S.S. | Requirement | Results |
|--|---|----------------|--|---|
| PRECONDITIONING OF SMD DEVICES Before TC/THB/ENV. SEQ. | DRYNG 1H @ 125°C STORE 168H @ TA=85°C RH=85% Reflow @ 260°C 3 times | 204 x 1 Lot | Parameter deviation within spec. limits at end of preconditioning. | No parameter deviation out of spec. limits at end of preconditioning. |
| H.T.S. | TA=175℃ | 77 x 1 Lot | Parameter deviation within spec. limits at 1000 hours. | No parameter deviation out of spec. limits at 1000 hours. |
| T.H.B. | D.U.T. SMD PRECONDITIONED TA=85℃ - RH=85% Vbias= 20V | 77 x 1 Lot | Parameter deviation within spec. limits at 1000 hours. | No parameter deviation out of spec. limits at 1000 hours. |
| H.T.R.B. | T.A.=175℃; Vdd=16V | 77 x 1 Lot | Parameter deviation within spec. limits at 1000 hours. | No parameter deviation out of spec. limits at 1000 hours. |
| H.T.F.B. | TA = 150℃ ; Vgss= 20V | 77 x 1 Lot | Parameter deviation within spec. limits at 1000 hours. | No parameter deviation out of spec. limits at 1000 hours. |
| PRESSURE POT | TA=121℃ - PA=2Atm | 77 x 1 Lot | Parameter deviation within spec. limits at 96 hours. | No parameter deviation out of spec. limits at 96 hours. |
| THERMAL CYCLES AIR TO AIR | D.U.T. SMD PRECONDITIONED TA=-65℃ TO 150℃ 1 HOUR / CYCLE | 77 x 1 Lot | Parameter deviation within spec. limits at 500 cycles. | No parameter deviation out of spec. limits at 500 cy |
| THERMAL FATIGUE | TC=105℃ - Pd=2W | 77 x 1 Lot | Parameter deviation within spec. limits at 10k cycles. | No parameter deviation out of spec. limits at 10Kcy. |
| ENVIRONMENTAL SEQUENCE | D.U.T. SMD PRECONDITIONED 100 THERMAL CYCLES + 96H PP | 50 x 1 Lot | Parameter deviation within spec. limits at end of test. | No parameter deviation out of spec. limits at end of test. |

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Technological Characteristics

D.U.T.: STD55NH2LLT4 LINE: 432C PACKAGE: DPAK

| DIE | Technology: Material: Metallization – Front : - Back : | PMOS 20V/14 mOl Silicon AlSiCu Ti-Ni-Au | nm SP3, 7 Masks Passivation : Dimensions : | |
|---------------|---|--|---|--|
| DIE ATTACH | Soft solder | FRAME | Frame and lead material: Frame coating : Lead coating : | Raw copper Sel Nickel on T- post Sn 100% |
| WIRE BOND | Ultrasonic | WIRE | Material : Diameter : | Al Gate; Al Source; 5 mils Gate; 15 mils Source |
| SEALING | Molding | PACKAGING | Material : | Epoxy resin |

PRODUCTION PLACES: WAFER PROCESSING: Catania

ASSEMBLY LOCATION : Shanghai - China Q.A. LOCATION : Shanghai - China

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Technological Characteristics

D.U.T.: STD17NF03LT4 LINE: E33N PACKAGE: DPAK

| DIE | Technology: Material: Metallization – Front : - Back : | Silicon AlSi | m, EHD2_C LV, 5 N Passivation : Dimensions : | NO Passivation |
|---------------|---|-----------------|---|--|
| DIE ATTACH | Soft solder | FRAME | Frame and lead material: Frame coating : Lead coating : | Raw copper Sel Nickel on T- post Sn 100% |
| WIRE BOND | Ultrasonic | WIRE | Material : Diameter : | Al Gate; Al Source; 5 mils Gate; 10 mils Source |
| SEALING | Molding | PACKAGING | Material : | Epoxy resin |

PRODUCTION PLACES: WAFER PROCESSING: AngMokio - Singapore ASSEMBLY LOCATION: Shanghai - China

Q.A. LOCATION : Shanghai - China

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Technological Characteristics

D.U.T.: STD38NH02LT4 LINE: 3L2B PACKAGE: DPAK

| DIE | Technology: Material: Metallization – Front : - Back : | PMOS 20V/18 mOh Silicon AlSi Ti-Ni-Au | nm EHD3, 6 Masks Passivation : Dimensions : | |
|---------------|---|--|---|--|
| DIE ATTACH | Soft solder | FRAME | Frame and lead material: Frame coating : Lead coating : | Raw copper Sel Nickel on T- post Sn 100% |
| WIRE BOND | Ultrasonic | WIRE | Material : Diameter : | Al Gate; Al Source; 5 mils Gate; 10 mils Source |
| SEALING | Molding | PACKAGING | Material : | Epoxy resin |

PRODUCTION PLACES: WAFER PROCESSING: Catania

ASSEMBLY LOCATION : Shanghai - China Q.A. LOCATION : Shanghai - China

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Reliability Test Description

High Temperature Reverse Bias (HTRB)

This test is performed in order to demonstrate the quality and reliability of devices subjected to an elevated temperature and simultaneously reverse biased. The purpose of this test is to detect surface defects such as poor passivation, presence of contaminants, etc...

High Temperature Forward Bias (HTFB)

This test is performed in order to demonstrate the quality and reliability of devices subjected to an elevated temperature and simultaneously forward gate biased. The purpose of this test is to detect surface and gate oxide defects.

High Temperature Storage (HTS)

This stress test is performed to check the device life in a high temperature ambient. Specimens are put for a period of time inside a stove in free air. Detectable failure mechanisms are presence of contaminants and metal corrosion.

Thermal Cycles/Shocks

The purpose of this test is to determine the resistance of devices to exposure to extreme changes in temperature. Specimens are first placed in a suitable environment at a low temperature and then transferred to one at high temperature. Effects of thermal cycles/shocks include cracking of die, breaking of wire bonding, mechanical damage to the device case.



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Reliability Test Description (continued)

Temperature Humidity Bias (THB)

This test is performed to check the device life in a high humidity ambient. Specimens are subjected to a permanent bias in a climatic chamber in the presence of steam. Detectable failure mechanisms are metal corrosion and moulding defects.

Pressure Pot

This test is performed in order to check device life in a high humidity ambient in an accelerated way. Specimens are subjected for a period of time inside an autoclave in the presence of steam and pressure. Detectable failure mechanism is metal corrosion.

Thermal Fatigue

This test is performed to demonstrate the quality and reliability of devices exposed to cyclic variation in electrical stress between "on" and "off" conditions and resultant cyclic variation in device and case temperatures (thermo-mechanical stress). The purpose of this test is to detect assembly defects: improper die-attach, bonding weakness and thermal mismatch among various components of the package.

Environmental Sequence

The purpose of this test is to study the influence of corrosion mechanism when the die/package system has already been stressed by temperature cycling.

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